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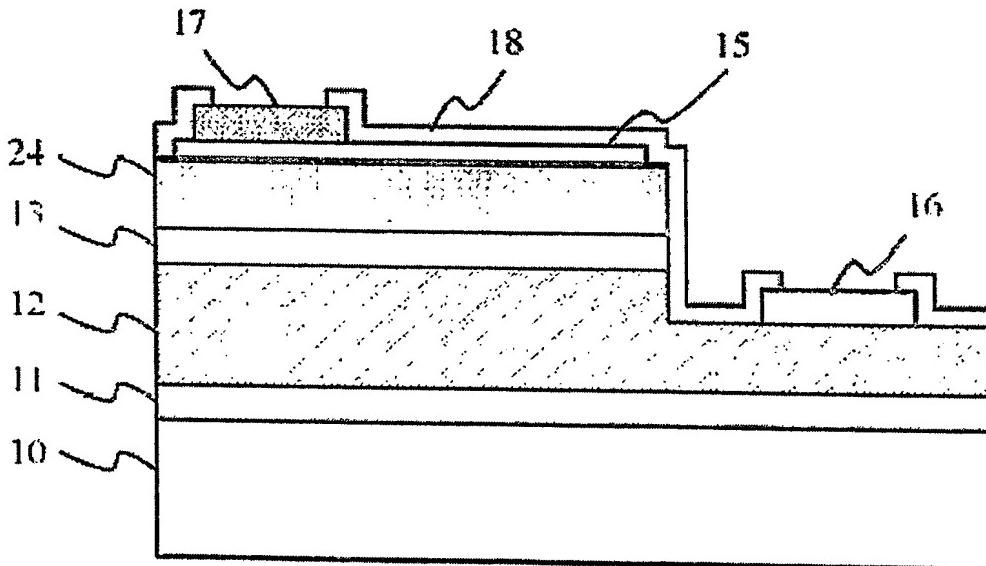
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(54) Title: NITRIDE SEMICONDUCTOR LIGHT EMITTING DEVICE



(57) Abstract: The present invention relates to a nitride semiconductor light emitting device including a plurality of nitride semiconductor layers with a p-type nitride semiconductor formed using as nitrogen precursor ammonia together with hydrazine-based material which upon thermal decomposition generates a radical being combined with a hydrogen radical to eliminate the hydrogen radical, thereby eliminates the need for a subsequent annealing process for removing hydrogen and prevents the active layer from being thermally damaged due to the subsequent annealing process.

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